**Features**

- Center amplifying gate
- Metal case with ceramic insulator
- Low on-state and switching losses

Typical Applications

- AC controllers
- DC and AC motor control
- Controlled rectifiers

Part No. H100KPE-KT100cT

$I_{T(AV)}$	6000A
V_{DRM}, V_{RRM}	1600V 1800V
	2000V 2200V
I_{TSM}	80 kA

SYMBOL	CHARACTERISTIC	TEST CONDITIONS	$T_j(^{\circ}C)$	VALUE			UNIT
				Min	Type	Max	
$I_{T(AV)}$	Mean on-state current	180° half sine wave 50Hz Double side cooled, $T_C=70^{\circ}C$	125			6000	A
I_{DRM} I_{RRM}	Repetitive peak current	at V_{DRM} at V_{RRM}	125			250	mA
I_{TSM}	Surge on-state current	10ms half sine wave	125			80	kA
I^2t	I^2t for fusing coordination	$V_R=0.6V_{RRM}$	125			32000	10^3A^2s
V_{TO}	Threshold voltage		125			0.82	V
r_T	On-state slope resistance		125			0.07	mΩ
V_{TM}	Peak on-state voltage	$I_{TM}=3000A, F=90kN$	25			1.10	V
dv/dt	Critical rate of rise of off-state voltage	$V_{DM}=67\%V_{DRM}$	125			2000	V/μs
di/dt	Critical rate of rise of on-state current	$V_{DM}=67\%V_{DRM}$ Gate pulse $t_r \leq 0.5\mu s$ $I_{GM}=1.5A$	125			200	A/μs
Q_{rr}	Recovery charge	$I_{TM}=2000A, t_p=4000\mu s, di/dt=-20A/\mu s, V_R=100V$	125		6000		μC
I_{GT}	Gate trigger current		25	40		300	mA
V_{GT}	Gate trigger voltage	$V_A=12V, I_A=1A$		0.8		3.0	V
I_H	Holding current			25		250	mA
V_{GD}	Non-trigger gate voltage	$V_{DM}=67\%V_{DRM}$	125			0.30	V
$R_{th(j-c)}$	Thermal resistance, Junction to case	Double side cooled				0.005	$^{\circ}C/W$
$R_{th(c-h)}$	Thermal resistance, case to heat sink	Clamping force 90kN				0.0015	
F_m	Mounting force			81		108	kN
T_{vj}	Junction temperature			-40		125	C
T_{stg}	Stored temperature			-40		140	C
W_t	Weight				1880		g
Outline	KT100cT						

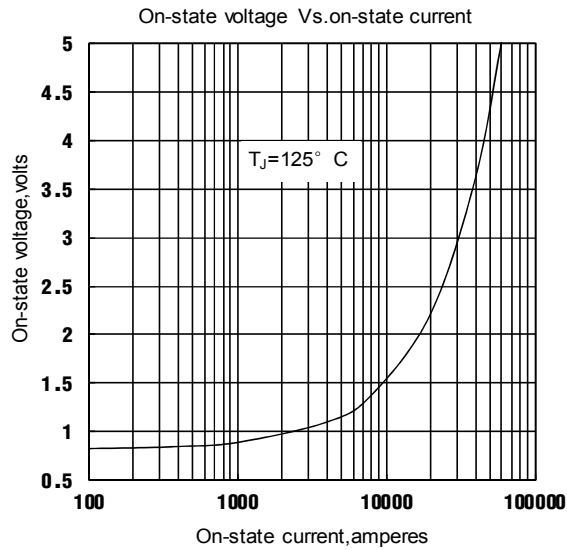


Fig.1

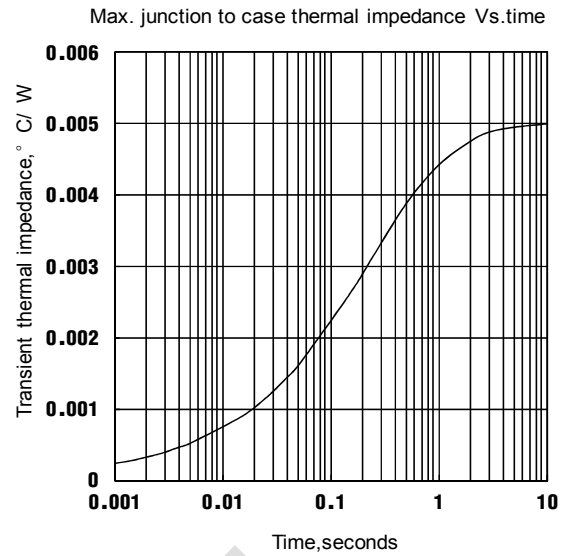


Fig.2

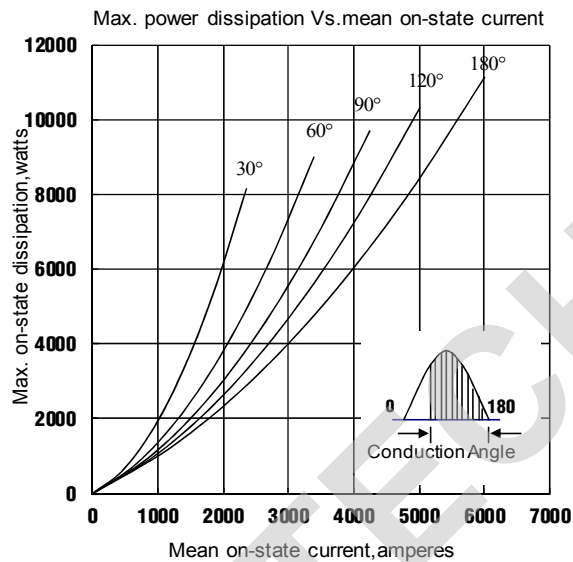


Fig.3

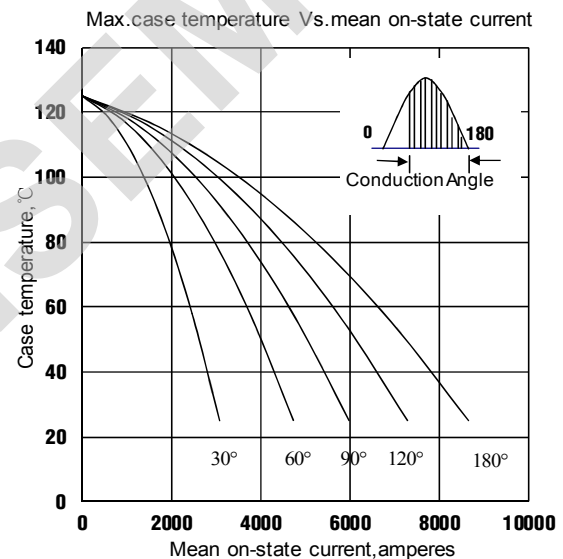


Fig.4

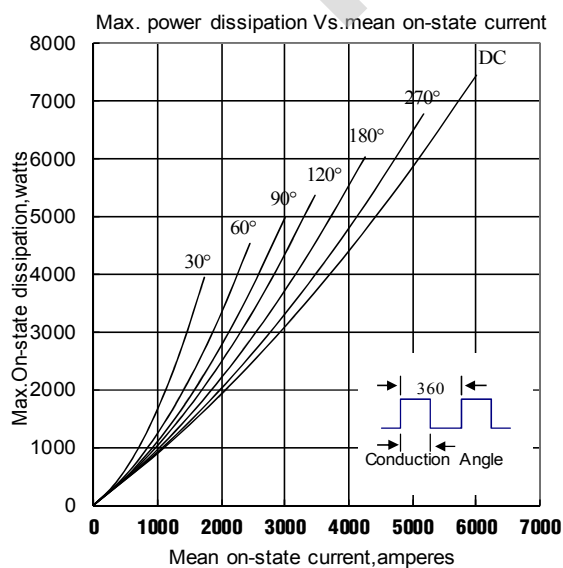


Fig.5

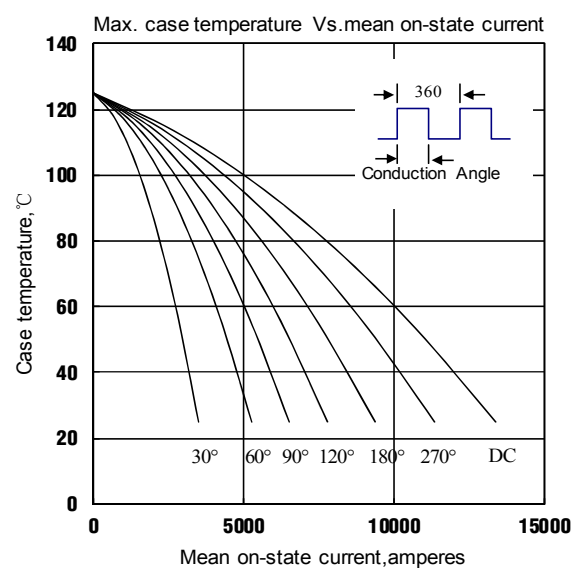


Fig.6

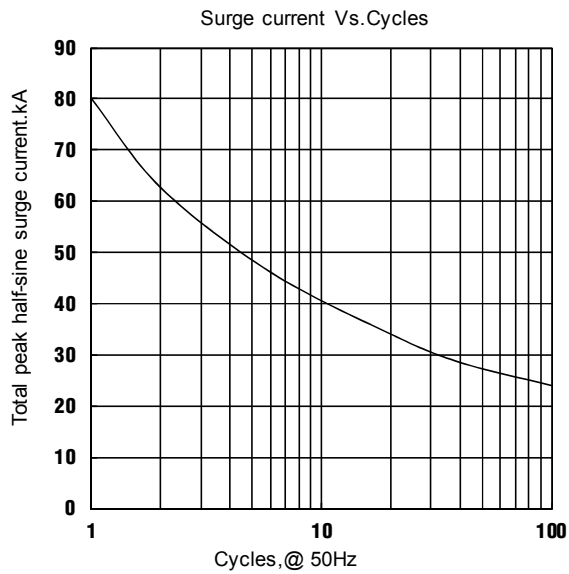


Fig.7

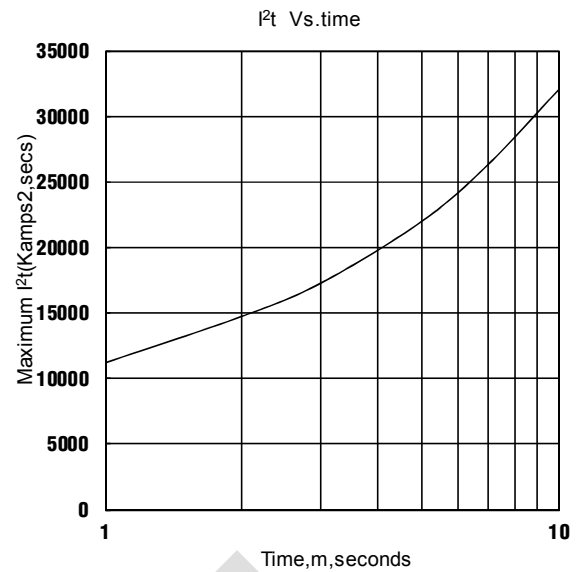


Fig.8

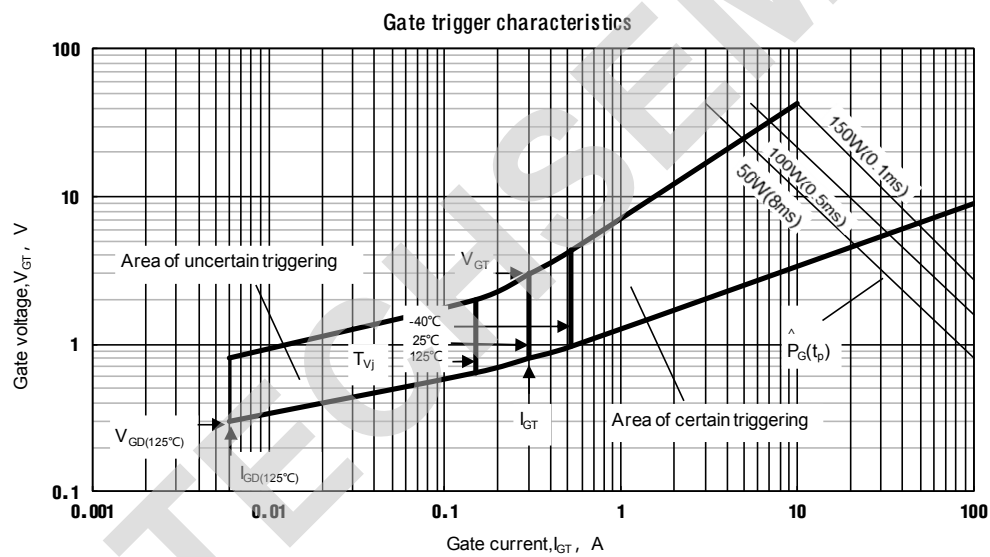


Fig.9

Outline:

